

Silicon NPN Power Transistors

2SC4150

DESCRIPTION

- With ITO-220 package
- Switching power transistor
- Low saturation voltage

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

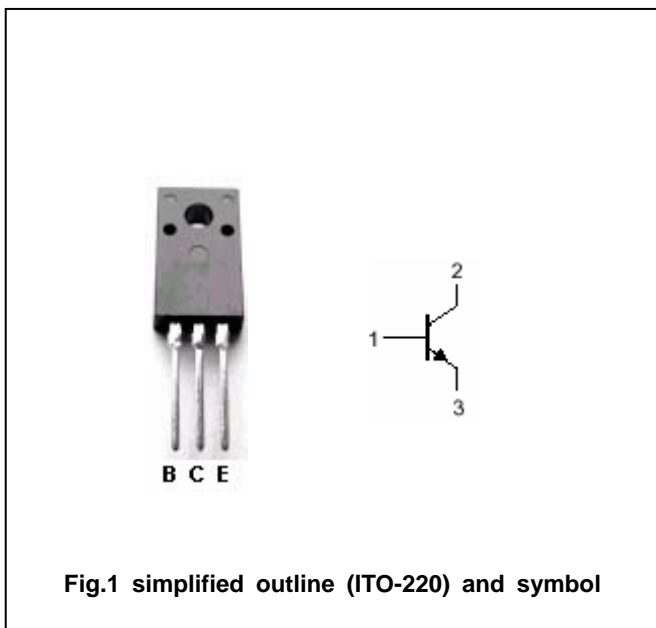


Fig.1 simplified outline (ITO-220) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	60	V
V _{CEO}	Collector-emitter voltage	Open base	40	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		12	A
I _{CM}	Collector current-Peak		24	A
I _B	Base current		2	A
I _{BM}	Base current-Peak		3	A
P _T	Total power dissipation	T _C =25	25	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-C}	Thermal resistance junction case	5.0	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	40			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A; I _B =0.3A			0.3	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A; I _B =0.3A			1.2	V
I _{CBO}	Collector cut-off current	At rated volatge			0.1	mA
I _{CEO}	Collector cut-off current					
I _{EBO}	Emitter cut-off current	At rated volatge			0.1	mA
h _{FE}	DC current gain	I _C =6A ; V _{CE} =2V	70			
f _T	Transition frequency	I _C =1.2A ; V _{CE} =10V		50		MHz
Switching times						
t _{on}	Turn-on time	I _C =6A; I _{B1} =0.6A I _{B2} =0.6A , R _L =5 V _{BB2} =4V			0.3	μs
t _s	Storage time				1.5	μs
t _f	Fall time				0.5	μs

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PACKAGE OUTLINE

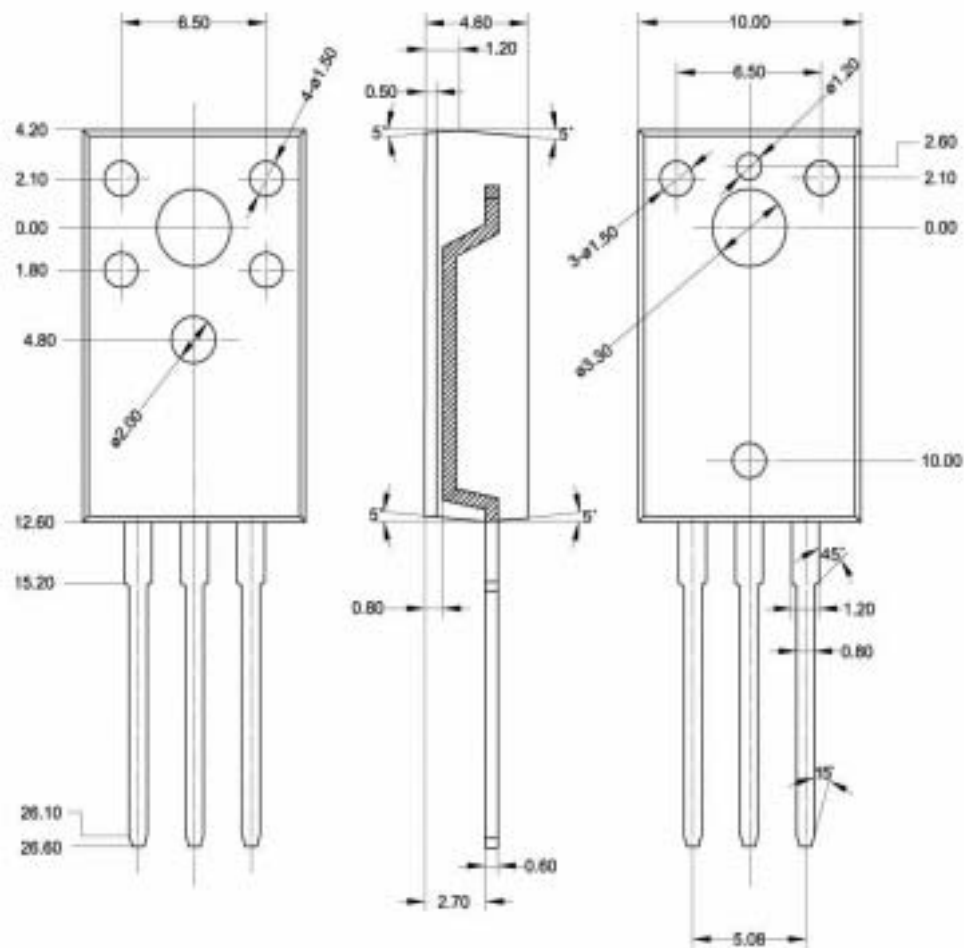


Fig.2 Outline dimensions (unindicated tolerance: ± 0.20 mm)